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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
							YES	МО
KMS	1	WO 02/27063 A2	04/04/02	PCT				

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)				
KMS	2	Shin et al., "Plasma-Enhanced Atomic Layer Deposition of SrTa ₂ O ₆ and SrBi ₂ Ta ₂ O ₉ Thin Films"; Atomic Layer Deposition (ALD 2002) Conference, Hanyang University, Seoul Korea, August 19-21, pp. 1-18 (2002)				
KMS	3	Williams et al. "Crystal Structure of Bi(OCMe ₂ CH ₂ Ome) ₃ and Its Use in the MOCVD of Bi ₂ O ₃ **"; Chemical Vapor Deposition; pp. 205-206 (2001)				
KMS	4	Gordon et al. "Vapor Deposition of Metal Oxides and Silicates: Possible Gate Insulators for Future Microelectronics"; Chem. Mater.; Vol. 13; pp. 2463-2464 (2001)				
KMS	5	Ritala et al. Chapter 2, "Atoic Layer Disposition"; Handbook of Thin Film Materials; Vol. 1: Deposition and Processing of Thin Films; pp. 103-159 (2002)				

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EXAMINER /Kelly Stouffer/

DATE CONSIDERED 07/27/2006

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